

Silicon NPN Power Transistors

2SC2706

DESCRIPTION

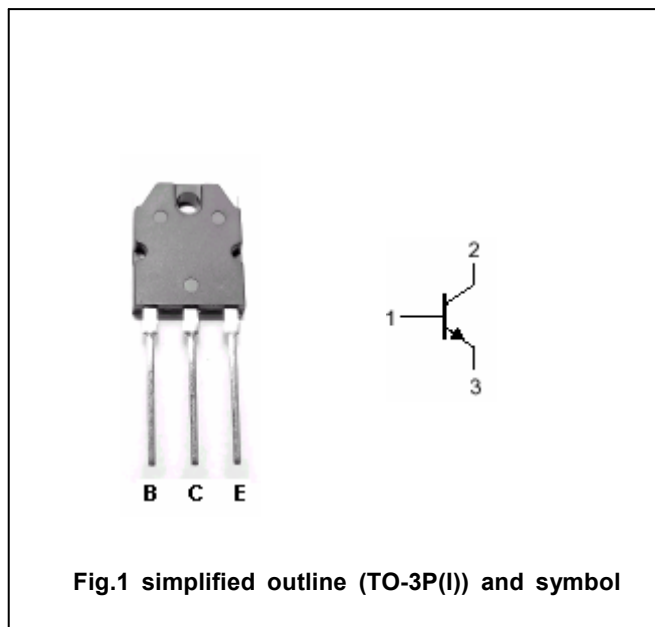
- With TO-3P(I) package
- High power dissipation

APPLICATIONS

- For audio power amplifier and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	140	V
V_{CEO}	Collector-emitter voltage	Open base	140	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		10	A
I_B	Base current		2	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	100	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Silicon NPN Power Transistors**2SC2706****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA, I_B=0$	140			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA, I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A; I_B=0.5A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=140V; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			10	μA
h_{FE-1}	DC current gain	$I_C=1A; V_{CE}=5V$	55		160	
h_{FE-2}	DC current gain	$I_C=5A; V_{CE}=5V$	35			
f_T	Transition frequency	$I_C=1A; V_{CE}=5V$		90		MHz

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PACKAGE OUTLINE

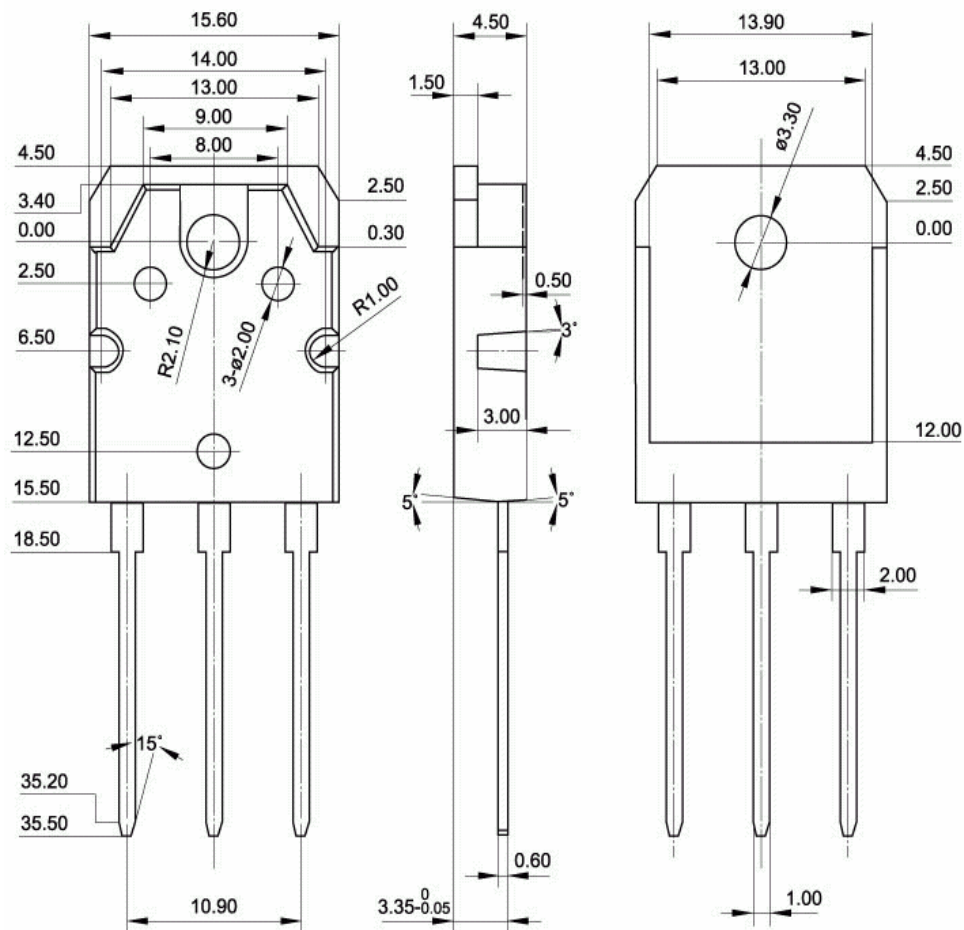


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)